



May 2000

QFET™

FQB27N25 / FQI27N25

250V N-Channel MOSFET

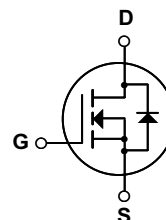
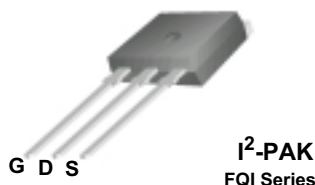
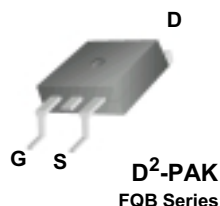
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

Features

- 25.5A, 250V, $R_{DS(on)} = 0.11\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 50 nC)
- Low C_{rss} (typical 45 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB27N25 / FQI27N25	Units
V_{DSS}	Drain-Source Voltage	250	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	25.5	A
	- Continuous ($T_C = 100^\circ\text{C}$)	16.2	A
I_{DM}	Drain Current - Pulsed (Note 1)	102	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	600	mJ
I_{AR}	Avalanche Current (Note 1)	25.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	3.13	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	180	W
	- Derate above 25°C	1.43	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	250	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.29	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 12.75\text{ A}$	--	0.083	0.11	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 12.75\text{ A}$ (Note 4)	--	24	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1900	2450	pF
C_{oss}	Output Capacitance		--	360	470	pF
C_{rss}	Reverse Transfer Capacitance		--	45	60	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{ V}, I_D = 27\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	32	75	ns
t_r	Turn-On Rise Time		--	270	550	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	170	ns
t_f	Turn-Off Fall Time		--	120	250	ns
Q_g	Total Gate Charge	$V_{DS} = 200\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	50	65	nC
Q_{gs}	Gate-Source Charge		--	12.5	--	nC
Q_{gd}	Gate-Drain Charge		--	26	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	25.5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	102	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 25.5 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 27 A,	--	220	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	1.8	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 1.5\text{ mH}, I_{AS} = 25.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 27\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

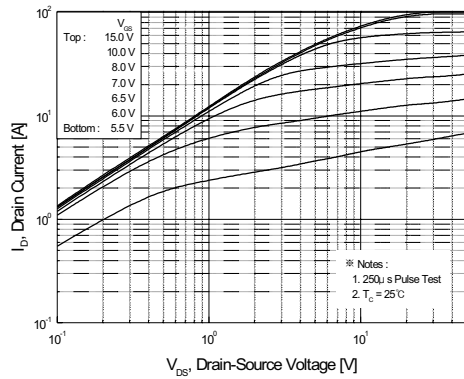


Figure 1. On-Region Characteristics

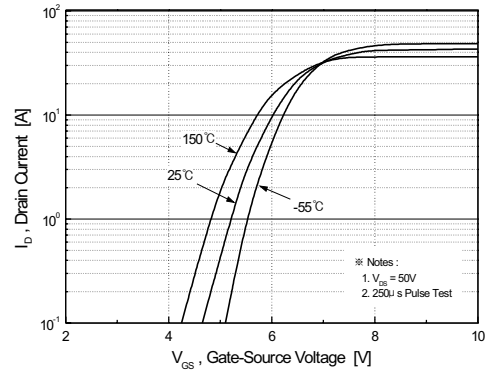


Figure 2. Transfer Characteristics

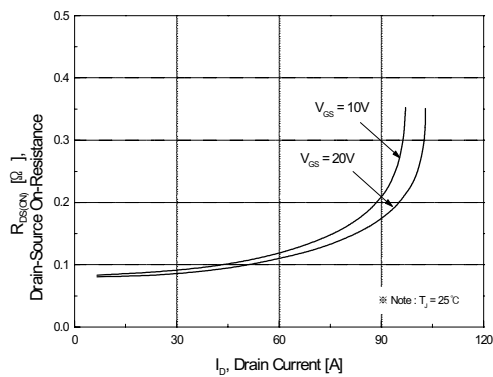


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

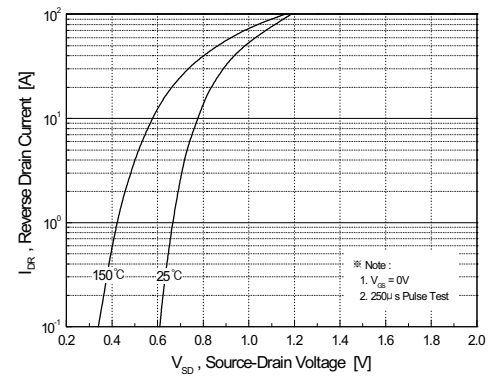


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

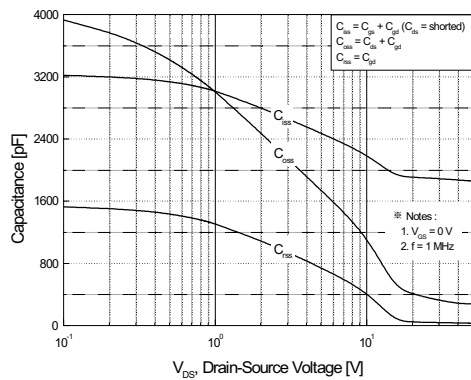


Figure 5. Capacitance Characteristics

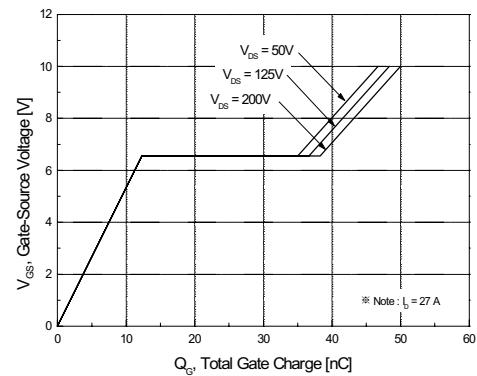


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

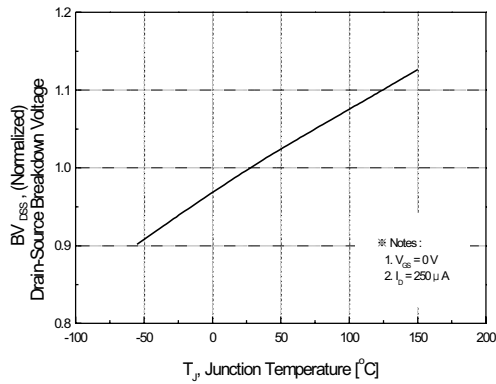


Figure 7. Breakdown Voltage Variation vs. Temperature

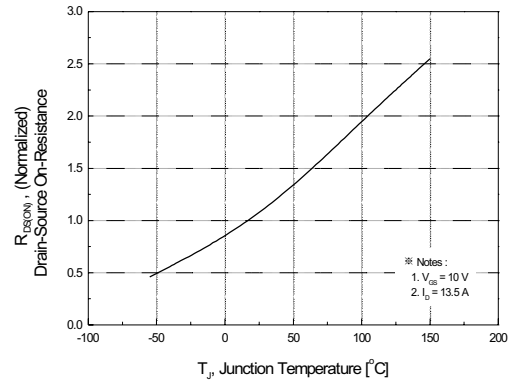


Figure 8. On-Resistance Variation vs. Temperature

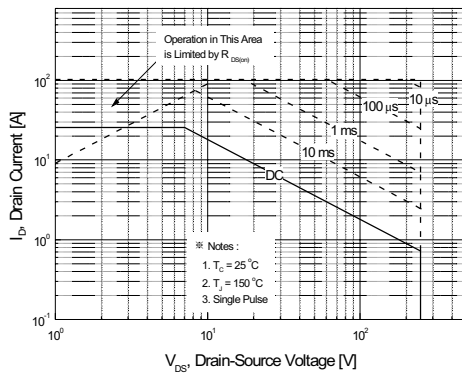


Figure 9. Maximum Safe Operating Area

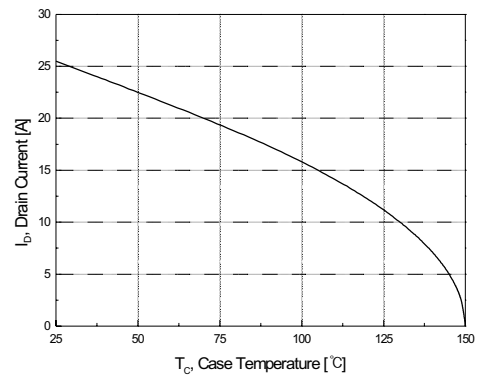


Figure 10. Maximum Drain Current vs. Case Temperature

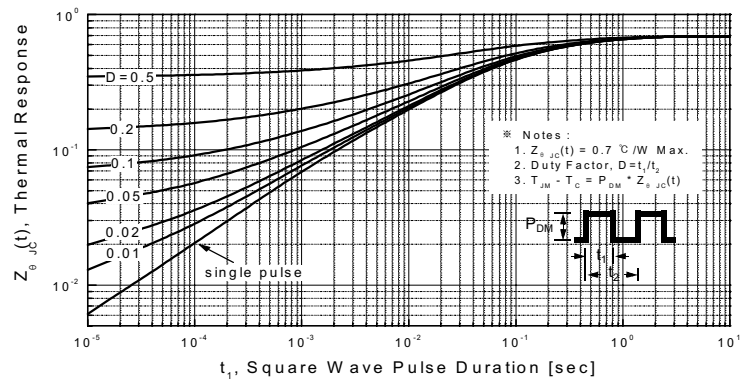
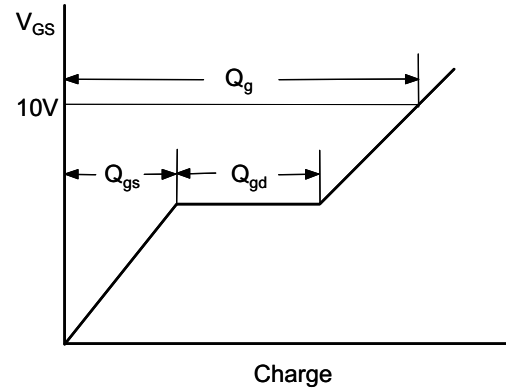
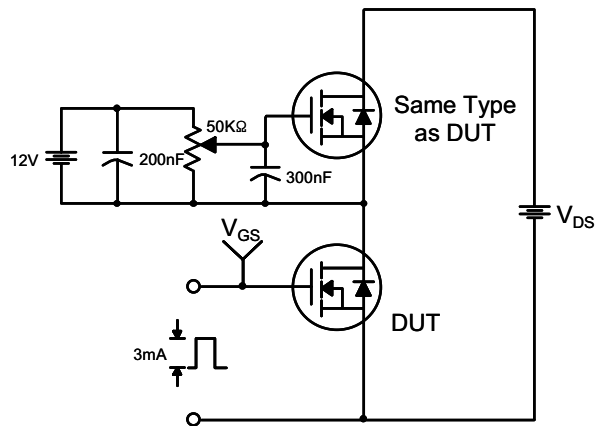
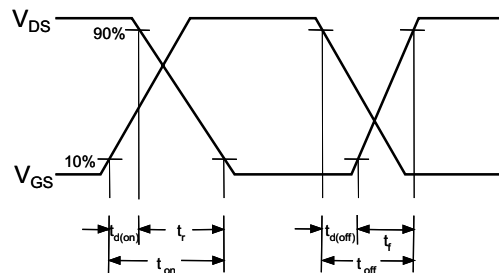
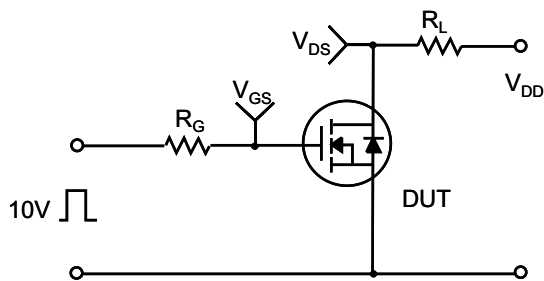


Figure 11. Transient Thermal Response Curve

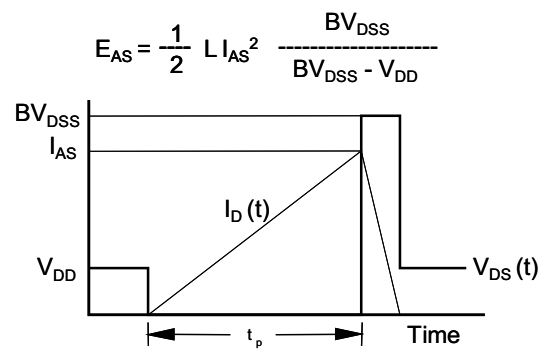
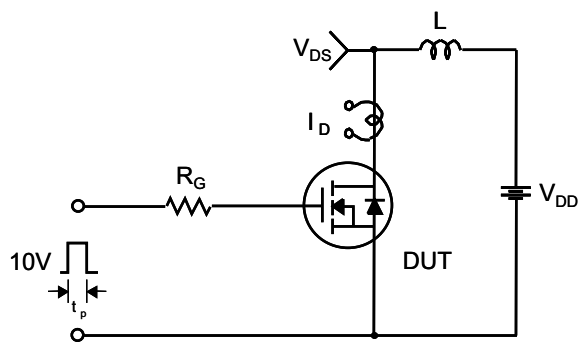
Gate Charge Test Circuit & Waveform



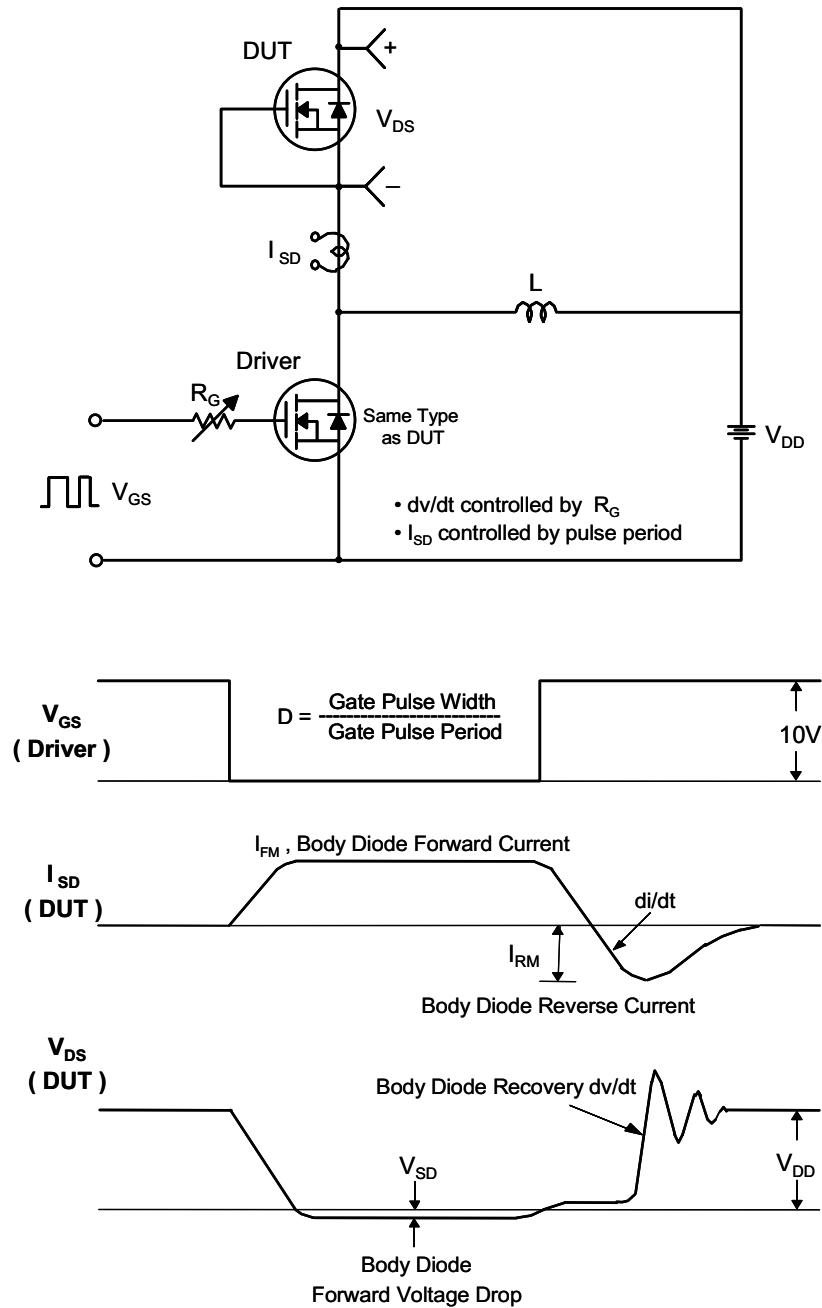
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Technical drawing of a rectangular component with four views: front, side, top, and bottom. Dimensions are provided in millimeters with tolerances and typical values in parentheses.

Front View:

- Overall width: 9.90 ± 0.20
- Overall height: 15.30 ± 0.30
- Top flange height: 1.20 ± 0.20
- Body height: 9.20 ± 0.20
- Bottom flange height: 4.90 ± 0.20
- Left side height: 1.40 ± 0.20
- Top left corner radius: (0.40)
- Left side hole diameter: 1.27 ± 0.10
- Right side hole diameter: 0.80 ± 0.10
- Left side hole offset: 2.54 TYP
- Right side hole offset: 2.54 TYP

Side View:

- Overall width: 4.50 ± 0.20
- Top flange width: $1.30^{+0.10}_{-0.05}$
- Body width: 0.10 ± 0.15
- Bottom flange width: 2.40 ± 0.20
- Left side height: 2.00 ± 0.10
- Left side hole diameter: (0.75)
- Bottom flange height: 2.54 ± 0.30
- Bottom flange width: $0.50^{+0.10}_{-0.05}$
- Bottom flange angle: $0^\circ \sim 3^\circ$

Top View:

- Overall width: 10.00 ± 0.20

Bottom View:

- Overall width: 10.00 ± 0.20
- Overall height: 15.30 ± 0.30
- Top flange height: (1.75)
- Body height: (7.20)
- Bottom flange height: 4.90 ± 0.20
- Left side height: 0.80 ± 0.10
- Top flange width: 10.00 ± 0.20
- Body width: (8.00)
- Bottom flange width: (4.40)
- Bottom flange radius: $(2 \times R0.45)$

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE^xTM
BottomlessTM
CoolFETTM
CROSSVOLTTM
E²CMOSTM
FACTTM
FACT Quiet SeriesTM
FAST[®]
FAST^rTM
GTOTM

HiSeCTM
ISOPLANARTM
MICROWIRETM
POPTM
PowerTrench[®]
QFETTM
QSTM
Quiet SeriesTM
SuperSOTTM-3
SuperSOTTM-6

SuperSOTTM-8
SyncFETTM
TinyLogicTM
UHCTM
VCXTM

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to

result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.